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PATENT
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	Willis, Stephen L.)	Group Art Unit 2815
)	
Appl. No.	:	09/552,383)	
)	
Filed	:	04/19/2000)	
)	
For	:	CHEMICAL MECHANICAL)	
		PLANARIZATION OF)	
		CONDUCTIVE MATERIAL)	
)	
Examiner	:	Diaz, Jose R.)	
)	

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Office Action mailed March 14, 2002 (Paper No. 9), please amend the above-captioned application as follows.

IN THE CLAIMS:

Please add new claims as follows:

56. (New) A method of forming a dielectric layer of a first thickness on a semiconductor wafer, the method comprising:

forming the dielectric layer of the first thickness on the wafer;
positioning a shield layer on the dielectric layer;
positioning a sacrificial layer on the shield layer;
depositing conductive material on the sacrificial layer;